



D2

S2

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

G2

Equivalent Circuit

Features

- Low Gate Charge
- Low R_{DS(ON)}:
 - 28mΩ @V_{GS} = 4.5V
 - $32m\Omega @V_{GS} = 2.5V$
 - $40m\Omega @V_{GS} = 1.8V$
 - Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- Green" Device (Note 4)

Mechanical Data

- Case: SOT-26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D

D1

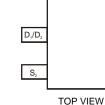
S1

- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4

G1

- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)





S

Pin Configuration

SOT-26

G,

 D_1/D_2

 G_2

Maximum Ratings @T_A = 25°C unless otherwise specified

J	•			
Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±8	V
Drain Current (Note 1) Continuous	T _A = 25°C T _A = 70°C	ID	4.2 3.2	A
Pulsed Drain Current (Note 2)		I _{DM}	30	А

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	PD	0.98	W
Thermal Resistance, Junction to Ambient (Note 1) t ≤10s	R _{0JA}	128	°C /W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s.

2. Repetitive Rating, pulse width limited by junction temperature.

3. No purposefully added lead.

4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.



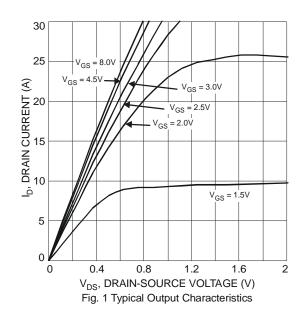
Electrical Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

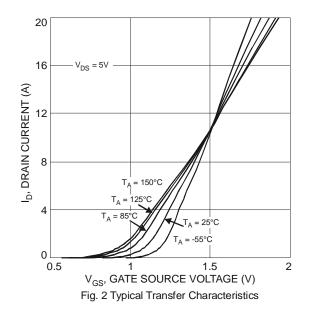
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
STATIC CHARACTERISTICS	Cymbol			max	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		V	$I_{D} = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Body Leakage Current	IGSS			±100	nA	$V_{DS} = 0V, V_{GS} = \pm 8V$
Gate Threshold Voltage	V _{GS(th)}	0.5		0.9	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance (Note 5)	R _{DS (ON)}		22 25 31	28 32 40	mΩ	$V_{GS} = 4.5V, I_D = 8.2A$ $V_{GS} = 2.5V, I_D = 3.3A$ $V_{GS} = 1.8V, I_D = 2.0A$
Forward Transfer Admittance	Y _{FS}	_	7		S	$V_{DS} = 10V$, $I_D = 4A$
Diode Forward Voltage (Note 5)	V _{SD}		0.7	0.9	V	I _S = 2.25A, V _{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 6)				•		·
Input Capacitance	C _{iss}	—	856		pF	
Output Capacitance	C _{oss}	_	83		pF	[−] V _{DS} = 10V, V _{GS} = 0V −f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		78		pF	
Gate Resisitance	R _G	s — 1.			Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$
SWITCHING CHARACTERISTICS						
Total Gate Charge	Qq		8.3	_	nC	
Gate-Source Charge	Q _{gs}	_	1.3		nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 8.2A
Gate-Drain Charge	Q _{ad}		3.1		nC	7
Turn-On Delay Time	t _{D(on)}		8.4		ns	
Turn-On Rise Time	tr		8.2		ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(off)}		40.4		ns	$R_L = 10\Omega, R_G = 6\Omega$
Turn-Off Fall Time	t _f		8.9		ns	7

Notes:

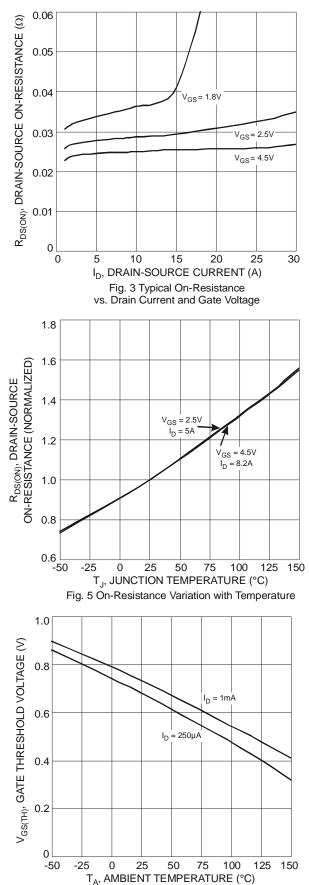
5. Test pulse width t = 300ms.

6. Guaranteed by design. Not subject to production testing.

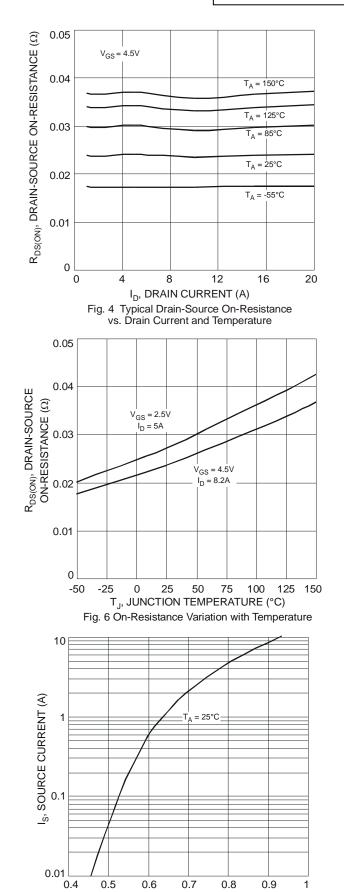










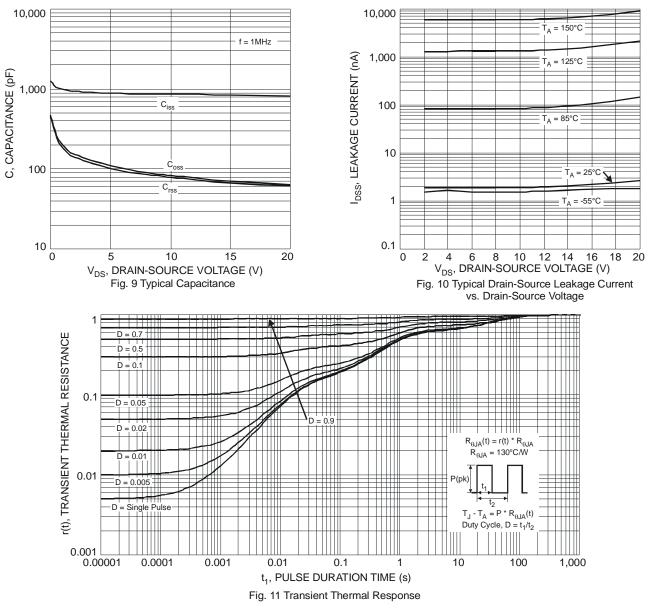


V_{SD}, SOURCE-DRAIN VOLTAGE (V) Fig. 8 Diode Forward Voltage vs. Current

DMG9926UDM Document number: DS31770 Rev. 4 - 2 Downloaded from Arrow.com.



DMG9926UDM



Ordering Information (Note 7)

Part Number	Case	Packaging
DMG9926UDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

	1	\square		_
	DN	lG	ΥM	
Γ				_

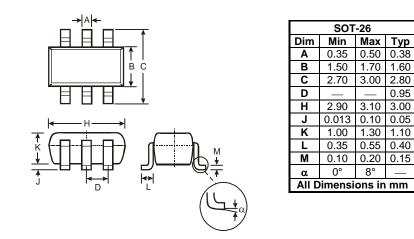
DMG = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

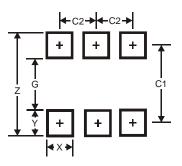
Year	2008		2009	2010		2011	2012		2013	2014	L. C.	2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

1.70

3.00

0.55

0.20

8°

1.60

2.80

0.95

3.00

0.40

0.15

1.30 1.10



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